



# STTH30L06

## TURBO 2 ULTRAFAST HIGH VOLTAGE RECTIFIER

**Table 1: Main Product Characteristics**

$I_{F(AV)}$	<b>30 A</b>
$V_{RRM}$	<b>600 V</b>
$T_j$	<b>175°C</b>
$V_F$ (typ)	<b>1.0 V</b>
$t_{rr}$ (max)	<b>65 ns</b>

### FEATURES AND BENEFITS

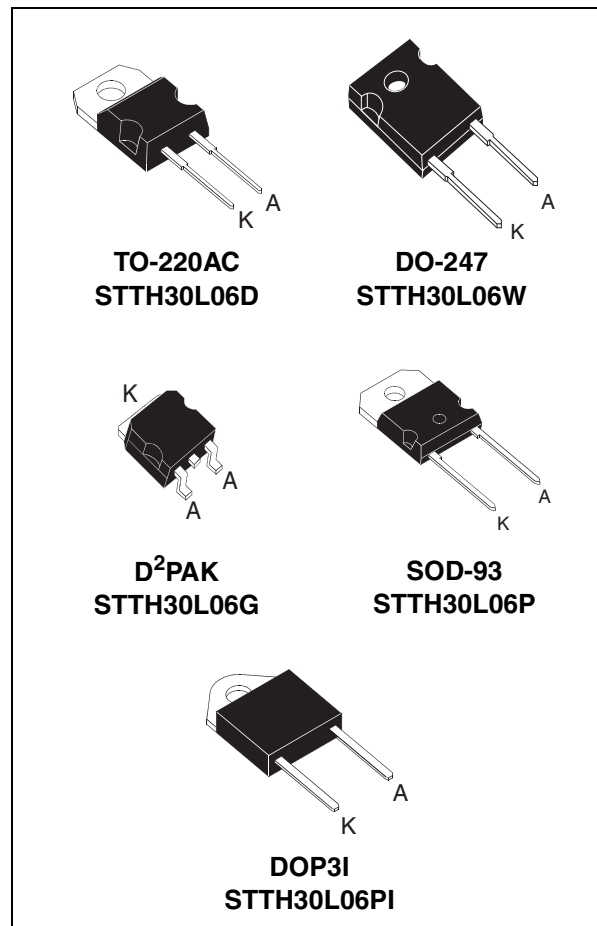
- Ultrafast switching
- Low reverse current
- Low thermal resistance
- Reduces switching & conduction losses

### DESCRIPTION

The STTH30L06, which is using ST Turbo 2 600V technology, is specially suited for use in switching power supplies, and industrial applications, as rectification and discontinuous mode PFC boost diode.

**Table 2: Order Codes**

Part Number	Marking
STTH30L06D	STTH30L06D
STTH30L06G	STTH30L06G
STTH30L06G-TR	STTH30L06G
STTH30L06W	STTH30L06W
STTH30L06P	STTH30L06P
STTH30L06PI	STTH30L06PI



## STTH30L06

**Table 3: Absolute Ratings** (limiting values)

Symbol	Parameter		Value	Unit	
$V_{RRM}$	Repetitive peak reverse voltage		600	V	
$I_{F(RMS)}$	RMS forward current		50	A	
$I_{F(AV)}$	Average forward current	TO-220AC / TO-247 / D <sup>2</sup> PAK / SOT-93	$T_c = 125^{\circ}\text{C}$ $\delta = 0.5$	30	A
		DOP3I	$T_c = 95^{\circ}\text{C}$ $\delta = 0.5$		
$I_{FSM}$	Surge non repetitive forward current		$t_p = 10\text{ms}$ sinusoidal	160	A
$T_{stg}$	Storage temperature range		-65 to + 175		$^{\circ}\text{C}$
$T_j$	Maximum operating junction temperature		175		$^{\circ}\text{C}$

**Table 4: Thermal Resistance**

Symbol	Parameter		Value (max.)	Unit
$R_{th(j-c)}$	Junction to case	TO-220AC / TO-247 / D <sup>2</sup> PAK / SOT-93	1.1	$^{\circ}\text{C}/\text{W}$
		DOP3I	1.7	

**Table 5: Static Electrical Characteristics**

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
$I_R^*$	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			25	$\mu\text{A}$
		$T_j = 150^{\circ}\text{C}$		80	800		
$V_F^{**}$	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 30\text{A}$			1.55	V
		$T_j = 150^{\circ}\text{C}$		1.0	1.25		

Pulse test: \*  $t_p = 5\text{ ms}$ ,  $\delta < 2\%$

\*\*  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

To evaluate the conduction losses use the following equation:  $P = 0.95 \times I_{F(AV)} + 0.010 I_{F(RMS)}^2$

**Table 6: Dynamic Characteristics**

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
$t_{rr}$	Reverse recovery time	$T_j = 25^{\circ}\text{C}$	$I_F = 0.5\text{A}$ $I_{rr} = 0.25\text{A}$ $I_R = 1\text{A}$			65	ns
			$I_F = 1\text{A}$ $di_F/dt = 50\text{ A}/\mu\text{s}$ $V_R = 30\text{V}$		65	90	
$I_{RM}$	Reverse recovery current	$T_j = 125^{\circ}\text{C}$	$I_F = 30\text{A}$ $V_R = 400\text{V}$ $di_F/dt = 100\text{ A}/\mu\text{s}$		11.5	16	A
$t_{fr}$	Forward recovery time	$T_j = 25^{\circ}\text{C}$	$I_F = 30\text{A}$ $di_F/dt = 100\text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$			500	ns
$V_{FP}$	Forward recovery voltage	$T_j = 25^{\circ}\text{C}$	$I_F = 30\text{A}$ $di_F/dt = 100\text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$		2.5		V

Figure 1: Conduction losses versus average forward current

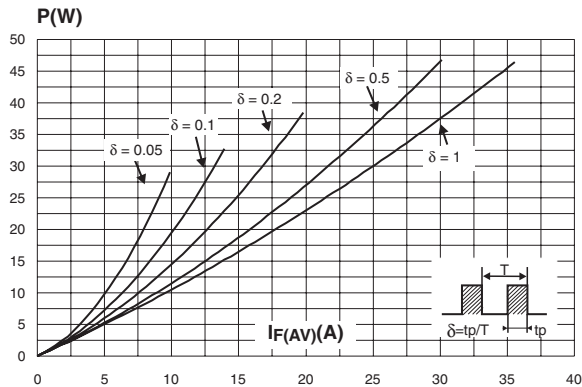


Figure 2: Forward voltage drop versus forward current

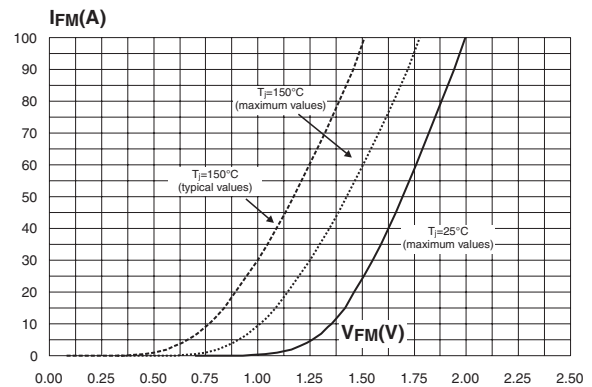


Figure 3: Relative variation of thermal impedance junction to case versus pulse duration

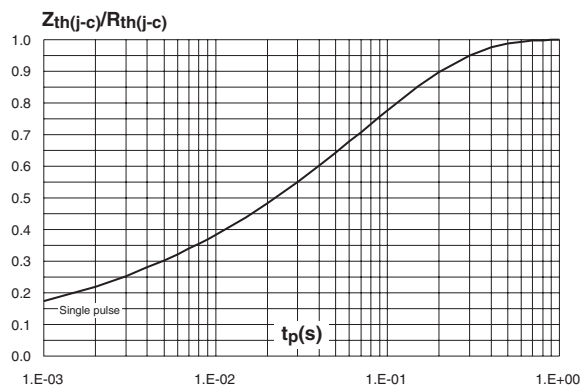


Figure 4: Peak reverse recovery current versus dIF/dt (typical values)

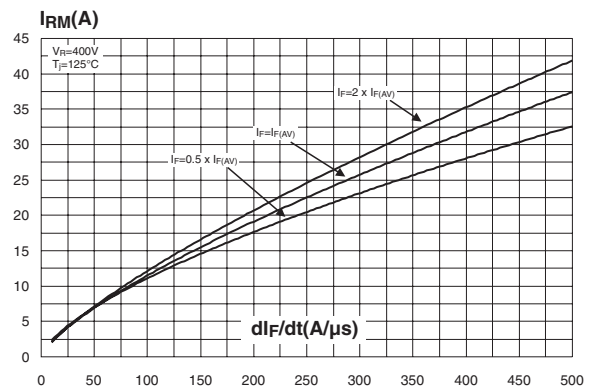


Figure 5: Reverse recovery time versus dIF/dt (typical values)

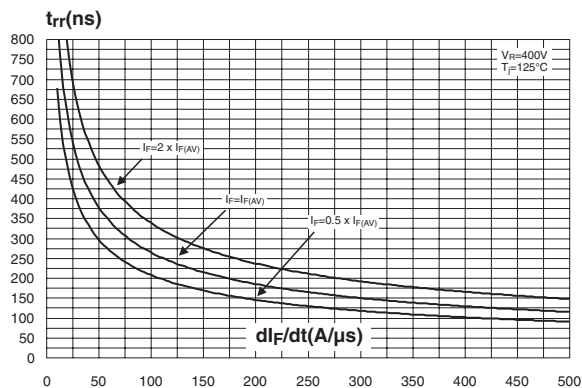


Figure 6: Reverse recovery charges versus dIF/dt (typical values)

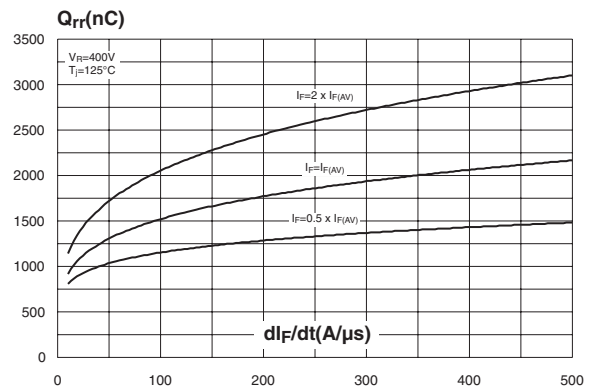


Figure 7: Reverse recovery softness factor versus  $di_F/dt$  (typical values)

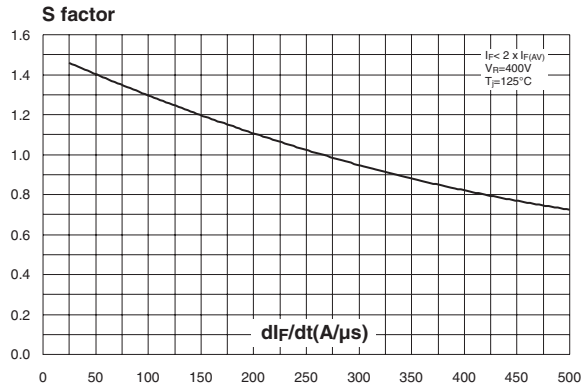


Figure 8: Relative variations of dynamic parameters versus junction temperature

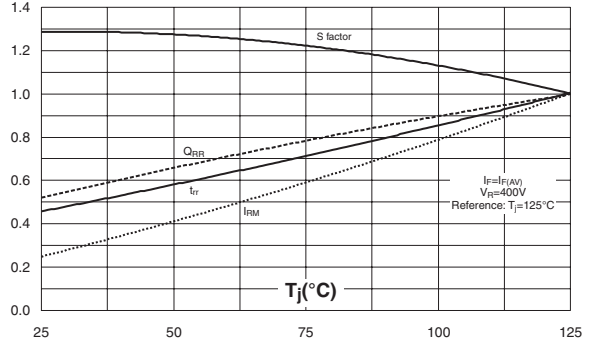


Figure 9: Transient peak forward voltage versus  $di_F/dt$  (typical values)

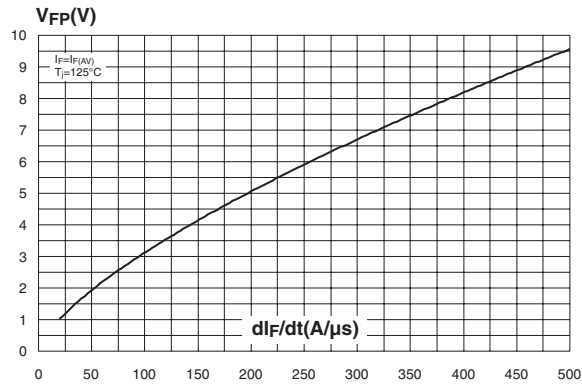


Figure 10: Forward recovery time versus  $di_F/dt$  (typical values)

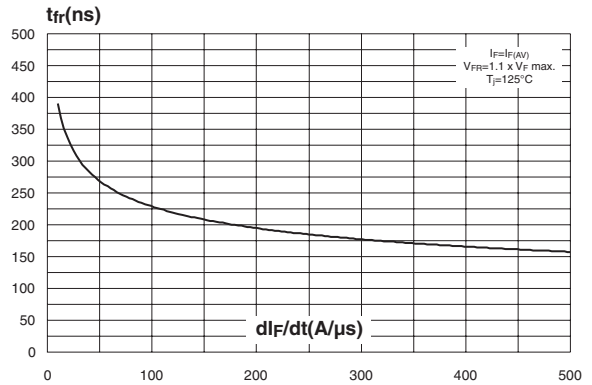


Figure 11: Junction capacitance versus reverse voltage applied (typical values)

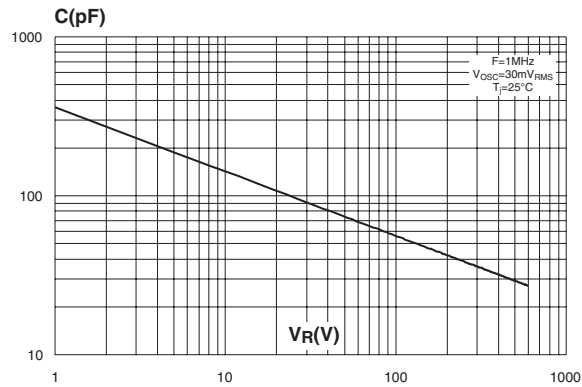


Figure 12: Thermal resistance junction to ambient versus copper surface under tab (epoxy FR4,  $e_{CU}=35\mu m$ ) (D<sup>2</sup>PAK)

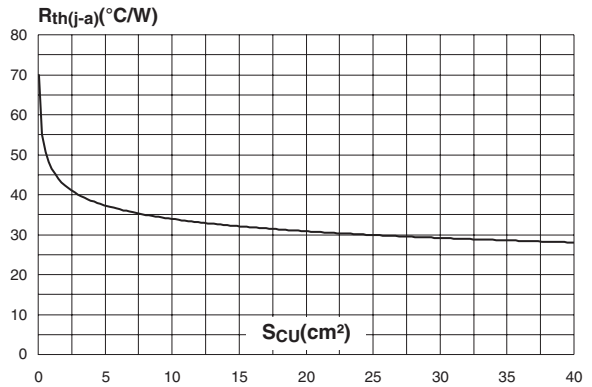


Figure 13: D<sup>2</sup>PAK Package Mechanical Data

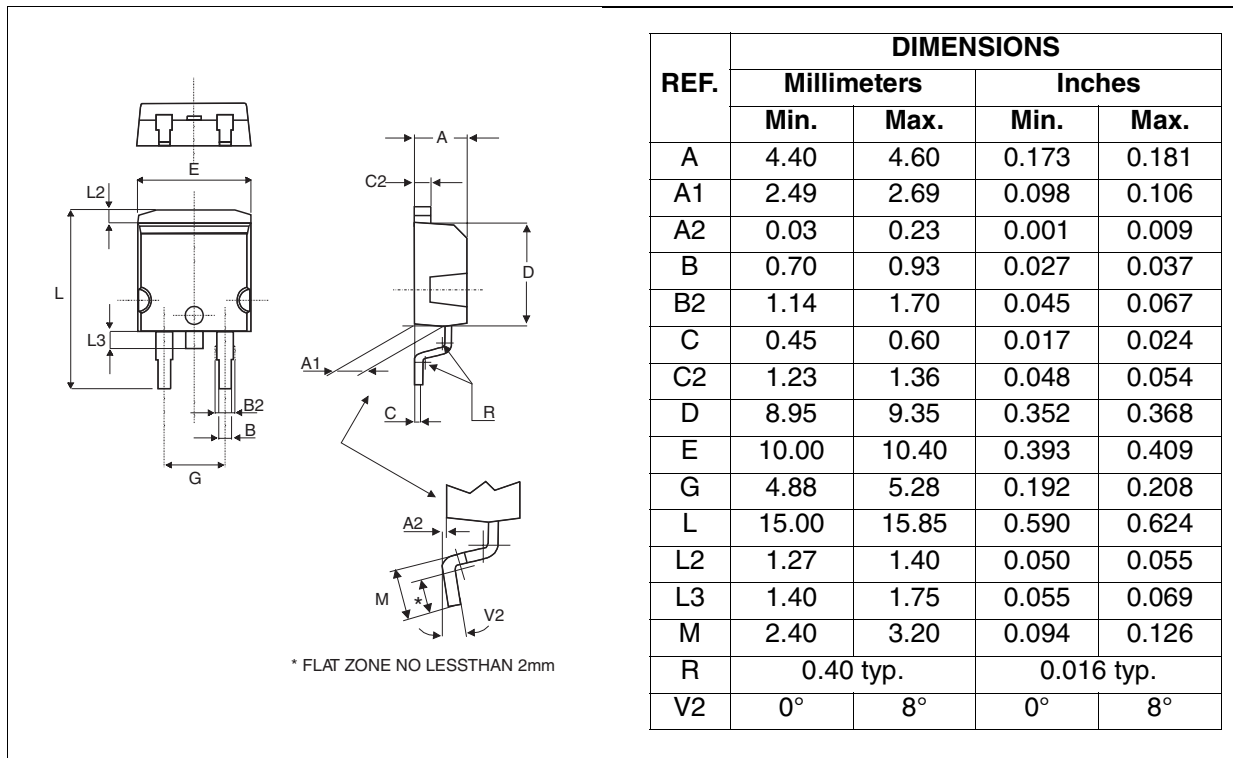


Figure 14: D<sup>2</sup>PAK Foot Print Dimensions (in millimeters)

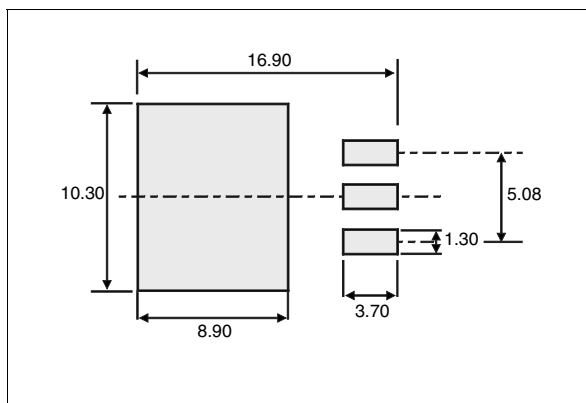


Figure 15: DO-247 Package Mechanical Data

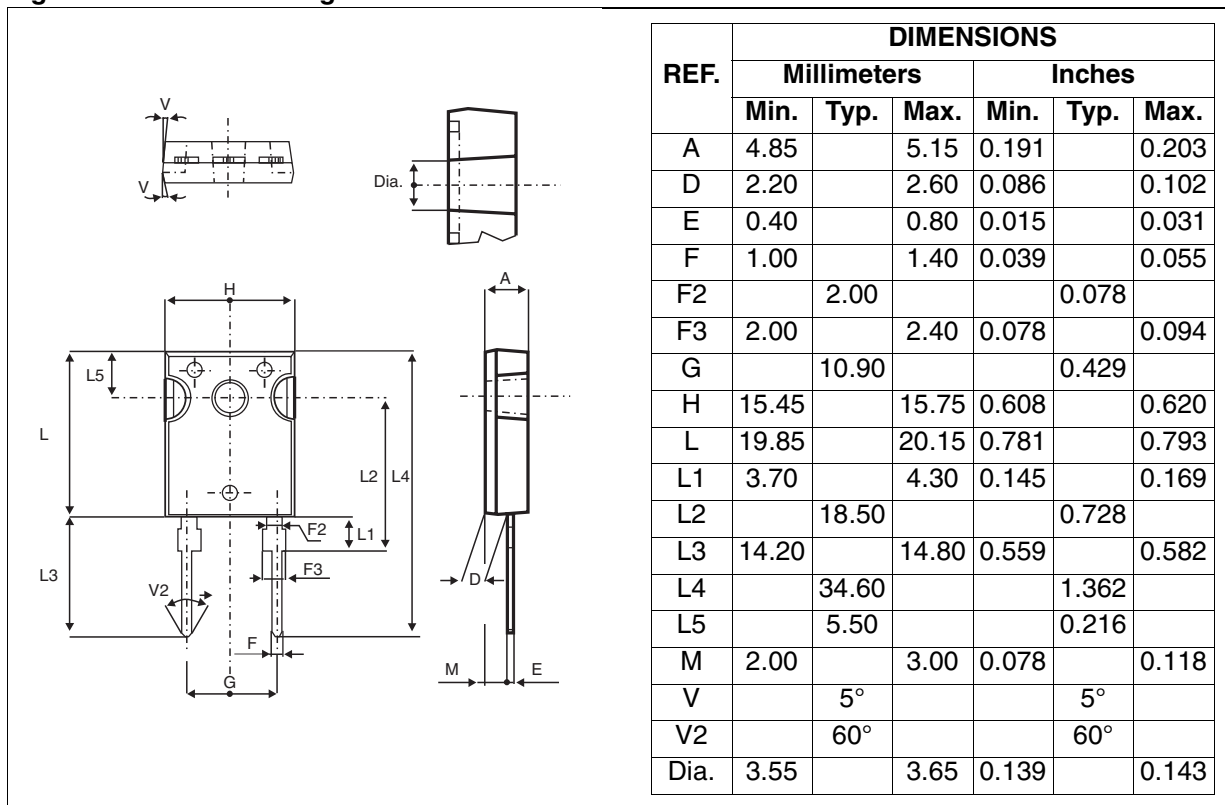


Figure 16: SOD-93 Package Mechanical Data

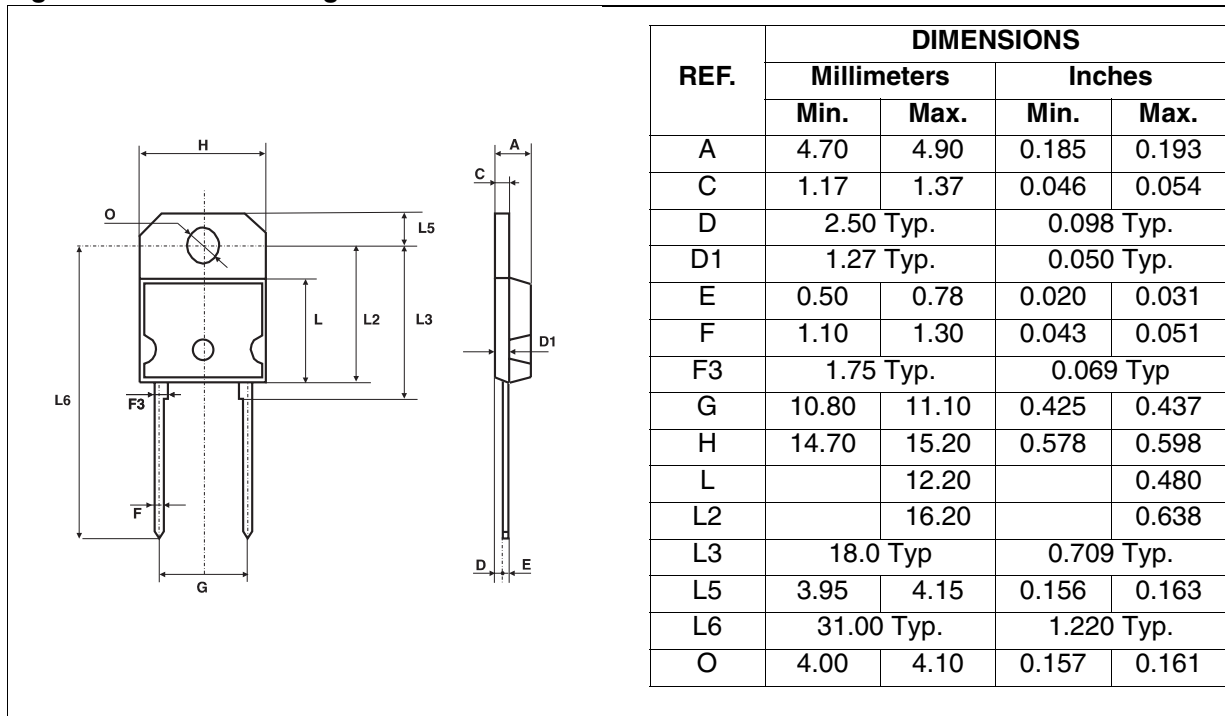


Figure 17: SOD-93 Package Mechanical Data

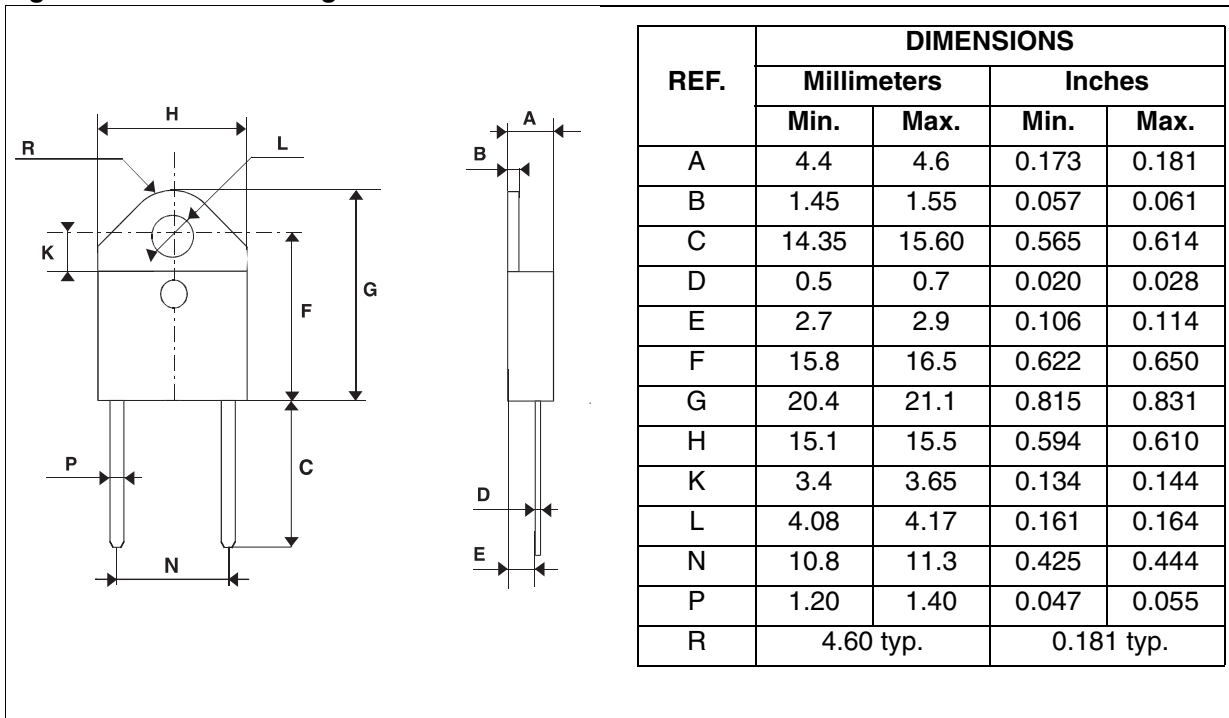


Figure 18: TO-220AC Package Mechanical Data

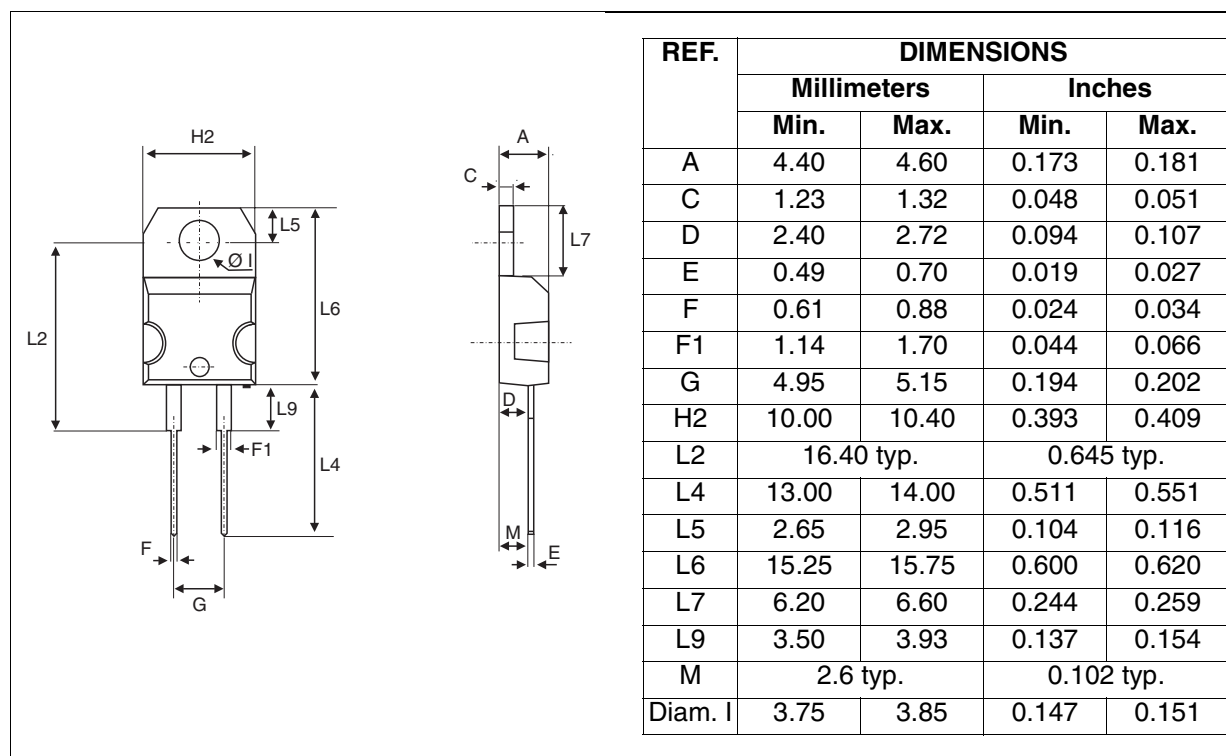


Table 7: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTH30L06D	STTH30L06D	TO-220AC	1.90 g	50	Tube
STTH30L06G	STTH30L06G	D <sup>2</sup> PAK	1.48 g	50	Tube
STTH30L06G-TR	STTH30L06G	D <sup>2</sup> PAK	1.48 g	1000	Tape & reel
STTH30L06W	STTH30L06W	DO-247	4.40 g	30	Tube
STTH30L06P	STTH30L06P	SOD-93	3.79 g	30	Tube
STTH30L06P	STTH30L06P	DOP3I	4.46 g	30	Tube

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.8 m.N. (TO-220FPAC) / 0.55 m.N. (TO-220AC)
- Maximum torque value: 1.0 m.N. (TO-220FPAC) / 0.70 m.N. (TO-220AC)

Table 8: Revision History

Date	Revision	Description of Changes
07-Sep-2004	1	First issue.
21-Oct-2004	2	DOP3I package added.
11-Jan-06	3	Table 3 on page 2: . $I_{F(RMS)}$ corrected from 30A to 50A . $I_{F(AV)}$ corrected from 50A to 30A



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